Abstracts

Sources of Non-Linearity in GaAs MESFET Frequency Multipliers

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E. Camargo, R. Soares, R.A. Perichon and M. Goloubkoff. "Sources of Non-Linearity in GaAs MESFET Frequency Multipliers." 1983 MTT-S International Microwave Symposium Digest 83.1 (1983 [MWSYM]): 343-345.

Transconductance and output conductance non-linearities of a single gate GaAs MESFET are used to define promising multiplier bias levels and harmonic loads. The model enables design of 25 mW 4-8 GHz doubler with 6 dB gain, 20 mW 4-12 GHz tripler with 3 dB gain and 2 mW 4-16 GHz quadruple with 2 dB gain.

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